

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Li, *et al.* Attorney Docket: 2004 P 50199 US
Filed: Herewith Examiner: TBD
Serial No.: TBD Art Unit: TBD
For: Transistor with Dopant-Bearing Metal in Source and Drain

Mail Stop: Patent Application
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

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The Applicants wish to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO/SB/08b that may be considered material to the examination of the above-identified application.

No fee is due at this time, as this Information Disclosure Statement is being filed concurrently with the patent application.

Respectfully submitted,



Kay Houston
Attorney for Applicants
Reg. No. 38,495

March 18, 2004

Date

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			Application Number	TBD	
			Filing Date	HEREWITH	
			First Named Inventor	Li	
			Art Unit	TBD	
			Examiner Name	TBD	
Sheet	1	of	1	Attorney Docket Number	2004 P 50199 US

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
	1	GANNAVARAM, S. <i>et al.</i> , "Low Temperature ($\leq 800^{\circ}\text{C}$) Recessed Junction Selective Silicon-Germanium Source/Drain Technology for sub-70 nm CMOS," 0-7803-6441-4/00, IEEE/North Carolina State University, Raleigh, NC, 2000.		
	2	HUANG, F.J., <i>et al.</i> , "Schottky-Clamped NMOS Transistors Implemented in a Conventional 0.8- μm CMOS Process," IEEE Electron Device Letters, September, 1998, pp. 326-328, Vol. 19, No. 9, IEEE, New York, NY.		
	3	"Front End Processes," International Technology Roadmap for Semiconductor (ITRS), 2002 Update, pp. 45-62, http://member.itrs.net/ .		
	4	"Front End Processes," International Technology Roadmap for Semiconductor (ITRS), 2003 Edition, pp. 23-25, http://member.itrs.net/ .		

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